

## R-C Thermal Model Parameters

### DESCRIPTION

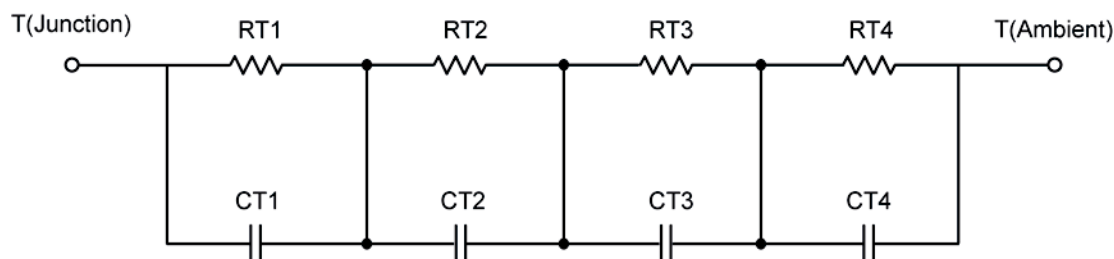
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

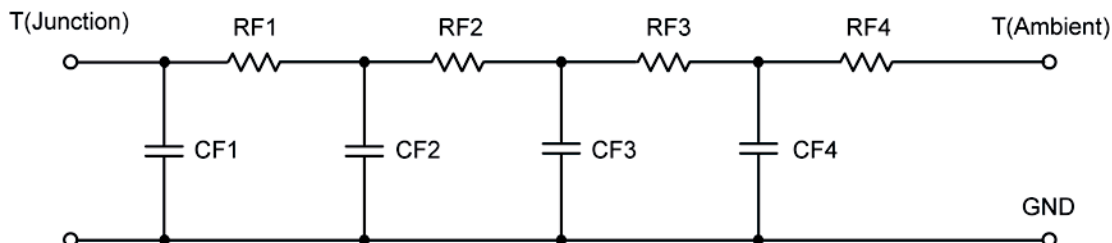
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	13.4389	N/A	6.3593
RT2	5.1108	N/A	944.9503 m
RT3	16.7765	N/A	3.3405
RT4	48.9638	N/A	10.3749
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	61.3750 m	N/A	15.0791 m
CT2	11.7026 m	N/A	6.7469 m
CT3	171.8818 m	N/A	877.7676 m
CT4	1.6999	N/A	87.9996 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	7.2845	N/A	1.8210
RF2	19.2687	N/A	8.9210
RF3	14.1189	N/A	8.2987
RF4	43.8469	N/A	1.9465
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	9.0889 m	N/A	3.5399 m
CF2	32.1476 m	N/A	12.0117 m
CF3	260.5862 m	N/A	100.2378 m
CF4	1.5615	N/A	471.6705 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

